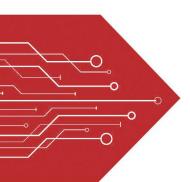
MSKSEMI















ESD

TVS

TSS

MOV

GDT

PLED

Broduct data sheet

GENERAL DESCRIPTION

LM321是一款单路输出的低功耗差分式运算放大器,可以单电源或双电源供电。具有较高的开环增益、内部补偿、高共模范围和良好的温度稳定性,以及具有输出短路保护的特点。可应用于传感器的放大电路、直流放大模块,音频放大电路和传统的运算放大电路中。

FEATURES

● 单电源电压范围: 3V~36V

● 双电源电压范围: ±18V

● 单位增益带宽:可达 1.2MHZ

● 输出短路保护

● 低功耗: 0.5mA @ V+=5V

● 封装形式: SOT23-5

APPLICATION

● 传感器信号放大器

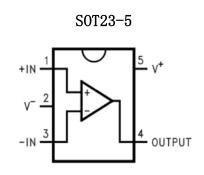
● 直流増益

● 音频放大器

● 其它应用领域

PIN CONFIGURATION

S0T23-5 管脚序号	管脚定义	功能说明
1	IN+	正相输入
2	V-	电源负
3	IN-	反相输入
4	OUTPUT	输出
5	V+	电源正



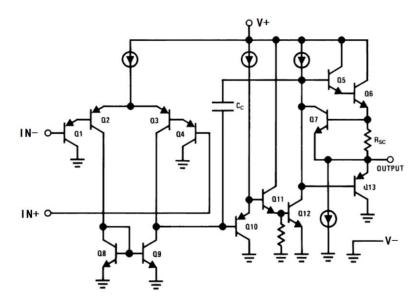
极限参数

项目	符号	极限值 ^⑴	单位
单电源供电电压	V+	40	V
双电源供电电压	Vs	±20	V
差分输入电压 (2)	V_{IDR}	±40	V
共模输入电压	$V_{\rm ICR}$	-0.3∼40V	V
输出短路时间	$t_{ m sc}$	连续	
耗散功率	P_D	300	mW
工作温度	T_{A}	0-70	$^{\circ}$
储存温度	Ts	-65-150	$^{\circ}$
焊接温度	Tw	260, 10s	$^{\circ}$

- 注: (1) 极限值是指无论在任何条件下都不能超过的极限值。如果达到此极限值,将有可能造成产品劣化等物理性损伤;同时在接近极限参数下,不能保证芯片可以正常工作。
 - (2) 输入IN+与IN-之间的电压差。



等效原理图



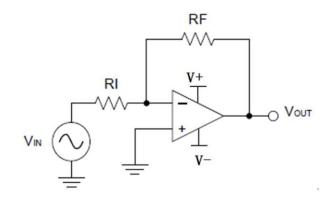
直流电学特性 (T_A=25℃, V+ =5V, V− =GND 除非特别指定)

项目	符号	测试条件		最小值	典型值	最大值	单位
输入失调电压	V _{IO}	$V+$ =5 V to MAX, $V_{IC}=V_{\mbox{ICR}}(\mbox{min})$, $VO=1.4V$		-	5	_	mV
输入失调电流	IIO	VO = 1.4 V		_	10	50	nA
偏置电流	${ m I}_{ t BIAS}$	VO = 1.4 V		-	50	250	nA
共模输入电压	V _{ICR}	V+=5V to 36V		V-	_	V+ −1.5V	V
开环电压增益	A _{OL}	V+=15V, VO=1V to 11V, RL≥2kΩ			100	_	V/mV
共模抑制比	CMRR	V+=5V to MAX, V _{IC} =V _{ICR} (min)		_	80	_	dB
单位增益带宽	GBWP			_	1.2	_	MHZ
电源电压抑制比 PssR	$\Delta V_{VDD}/\Delta V_{IO}$	V+=5V to MAX, f=20kHz		_	90	_	dB
输出高电平电压	VOH	V+ =15V, V _{ID} =1V	Iout =-50uA	_	13.6	_	V
			Iout =-1mA	_	13.5	_	V
			Iout =-5mA	_	13.4	_	V
		V+ =28V	RL=2k		26	-	V
	VOL	V+ =15V, V _{ID} =-1V	Iout =50uA	-	0.1	-	V
输出低电平电压			Iout =1mA	_	0.7	_	V
			Iout =5mA	_	1.0	_	V
		V+ =28V	RL=2k	_	0.85	_	V
中海工作 中冻	I _{CC}	V+ =5V, VO=1/2V+, No load		-	0.5	-	mA
电源工作电流		V+ =36, VO=1/2V+, No load		_	0.8	-	mA
单电源工作电压	V+	V- =0V (GND)		3	-	36	V
双电源工作电压	VS	V+, V-		-18	-	+18	V



典型应用

1、线路图



2、设计要求

必须选择大于输入电压范围和输出范围的电源电压。

例如,将信号源 VIN 从±0.5 V 放大到±1.8V。将电源设置为±5 V 足以适应此应用要求。

3、设计过程

根据公式(1)计算放大倍数(增益) Av

$$A_V = -VO/VIN$$
 ----(1)

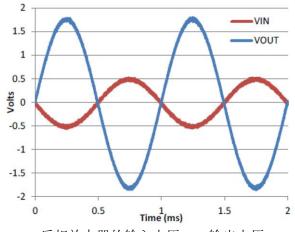
$$A_V = -VO/VIN = -1.8/0.5 = -3.6$$

一旦确定了所需的增益 Ay, 就要为 RI 或 RF 电阻选择一个值。根据运放的电特性及功耗的需要, 可选择 $1k\Omega-100k\Omega$ 范围内的值。本例将选择 $RI=10~k\Omega$,则 $RF=36k\Omega$ 。这由方程式 2 确定。

$$A_V = -RF/RI - - - - (2)$$

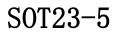
$$RF = -A_V * RI = 3.6*10 = 36 k \Omega$$

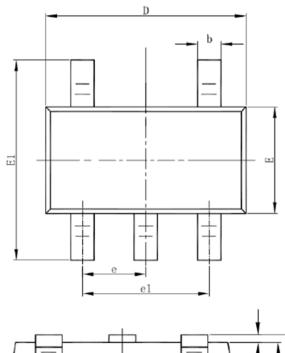
4、应用曲线图

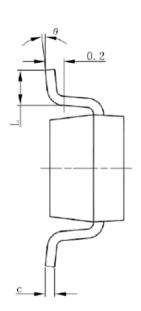


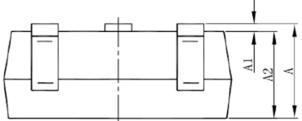
反相放大器的输入电压 VS 输出电压











S.,mh a I	Dimensions In	Millimeters	Dimensions	In Inches
Symbol	Min	Max	Min	Max
Α	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
С	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E	1.500	1.700	0.059	0.067
E1	2.650	2.950	0.104	0.116
е	0.950(BSC)	0.037(BSC)
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°

单位:英寸/毫米

REEL SPECIFICATION

P/N	PKG	QTY
LM321	SOT-23-5	3000





Semiconductor Compiance



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